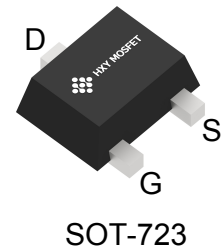




Description

The WNM2030-3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

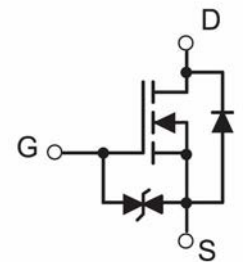


General Features

$V_{DS} = 20V$ $I_D = 1.2A$
 $R_{DS(ON)} < 260 m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 350 m\Omega @ V_{GS}=2.5V$
ESD Rating: 1500V HBM

Application

Battery protection
Load switch
Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
M2030-3	SOT-723	KF	8000

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	1.2	A
Pulsed Drain Current	I_{DM}	1.8	A
Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$



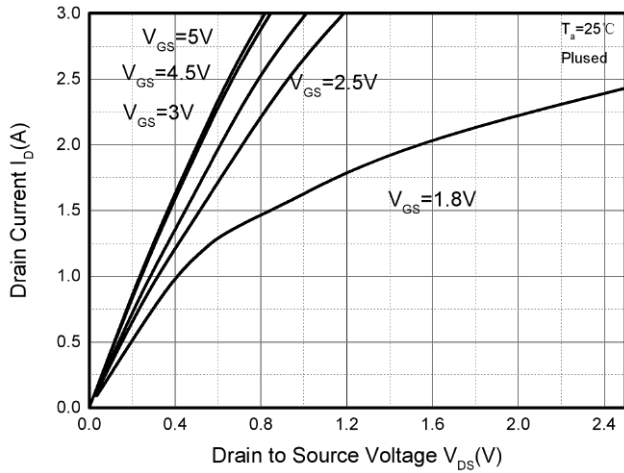
Electrical characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.3	0.65	1	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 1.2A$		150	260	m Ω
		$V_{GS} = 2.5V, I_D = 0.8A$		132	168	
		$V_{GS} = 1.8V, I_D = 0.3A$		165	240	
Input Capacitance	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V,$ $f = 1MHz$		79	120	pF
Output Capacitance	C_{oss}			13	20	
Reverse Transfer Capacitance	C_{rss}			9	15	
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 500mA, R_{GEN} = 10\Omega$		6.7		ns
Turn-on rise time	t_r			4.8		
Turn-off delay time	$t_{d(off)}$			17.3		
Turn-off fall time	t_f			7.4		
Body Diode Voltage	V_{SD}	$I_S = 0.5A, V_{GS} = 0V$		0.7	1.3	V

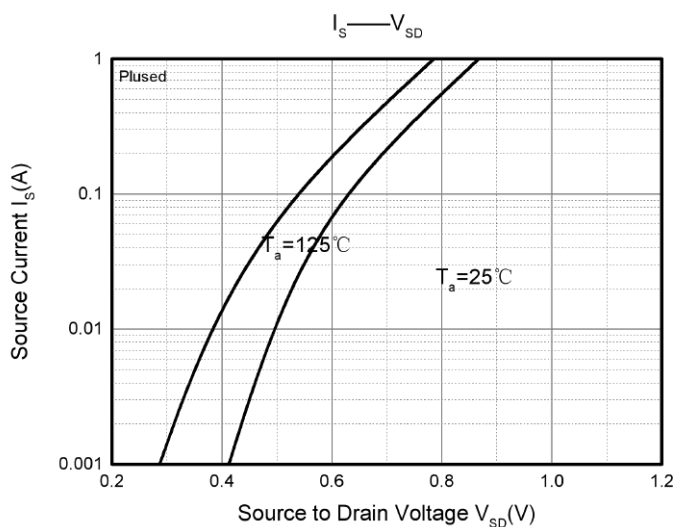
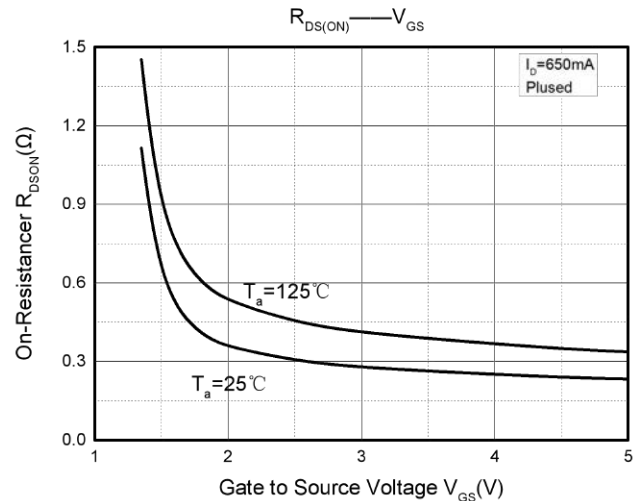
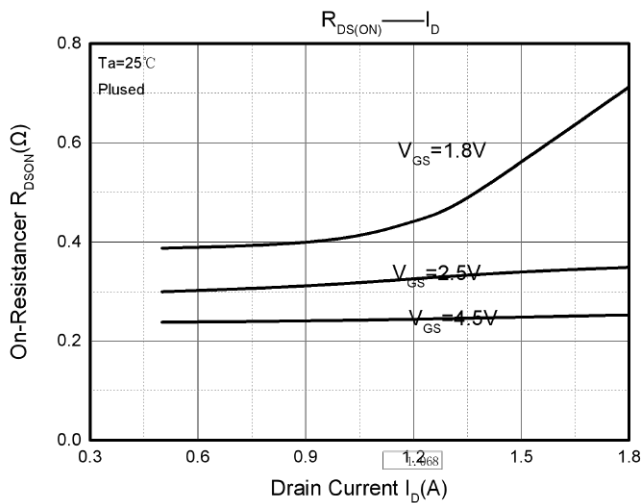
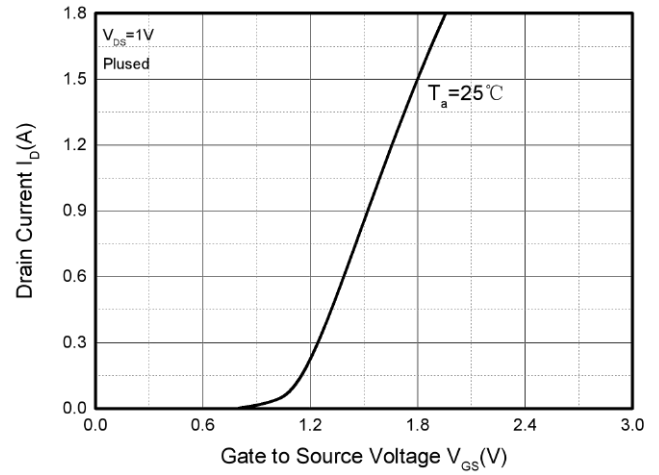


Typical Characteristics

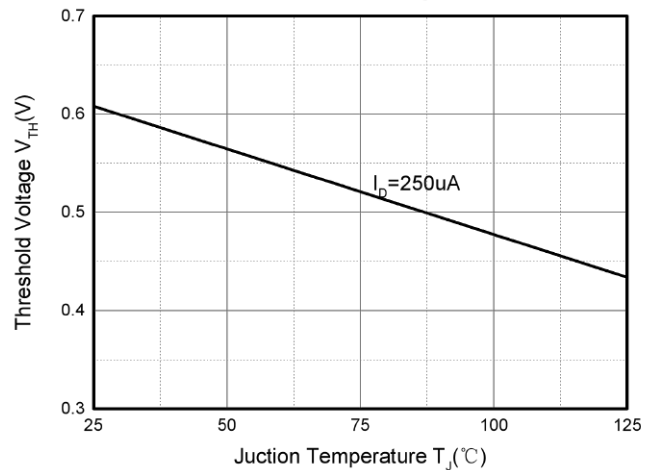
Output Characteristics



Transfer Characteristics

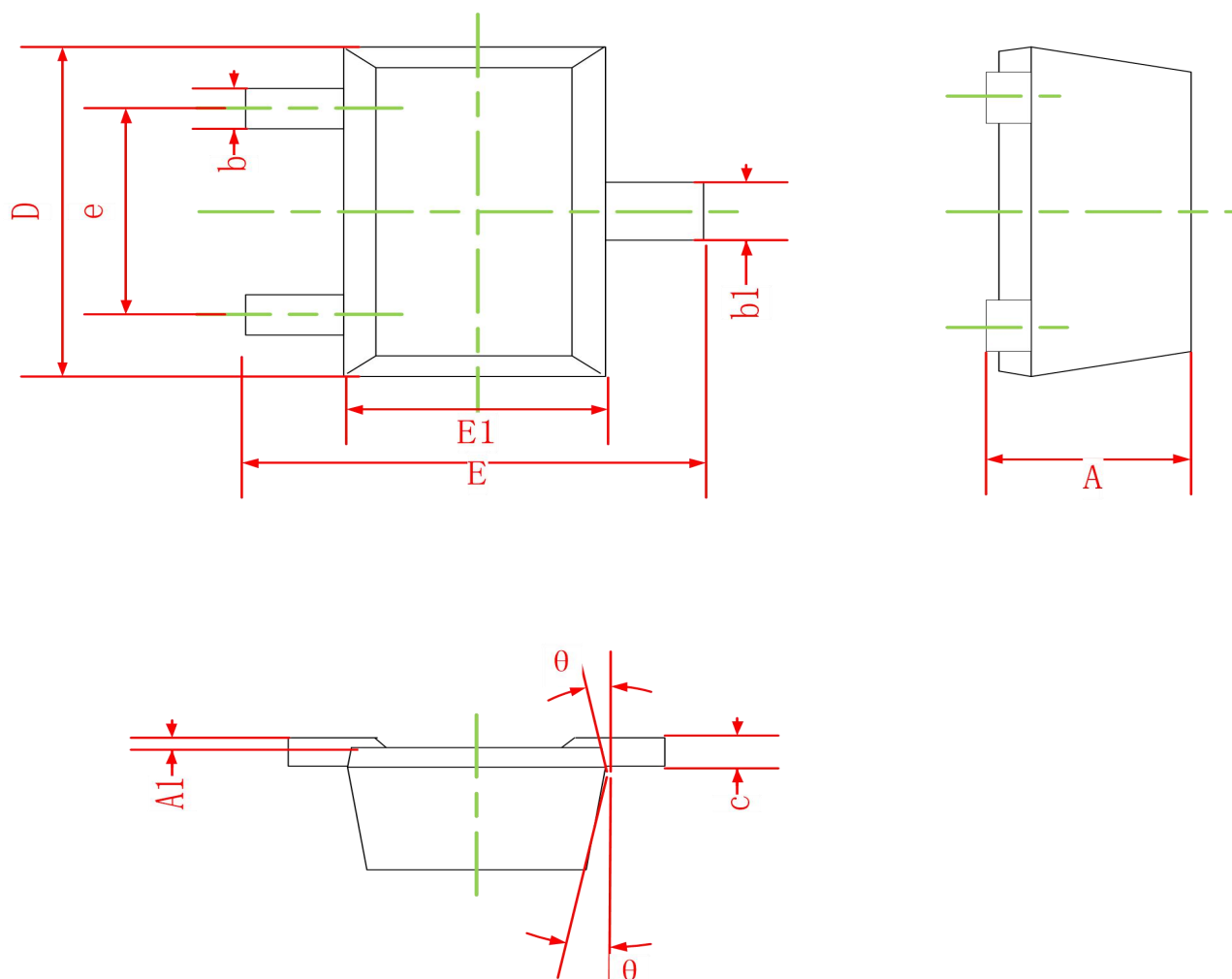


Threshold Voltage





SOT-723 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.430	0.500
A1	0.000	0.050
b	0.170	0.270
b1	0.270	0.370
c	0.080	0.150
D	1.150	1.250
E	1.150	1.250
E1	0.750	0.850
e	0.800TYP.	
θ	7° REF.	



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